

IN THE CLAIMS

Please amend the claims as follows:

Claims 1-5 (Canceled).

Claim 6 (Currently Amended): A semiconductor device comprising:

a semiconductor substrate;

an inductor provided with a first conductor interconnection formed spirally on the semiconductor substrate; and

a shield that is provided with a second conductor interconnection in a ring having a continuous configuration provided along an outer periphery of the spiral pattern of the inductor except for an opening in a portion of the second conductor interconnection, and the second conductor is electrically connected to ground potential, wherein

said shield includes a plurality of components with the plural components extending in corresponding plural planes, wherein

the plural components of the shield include a first and second component each having a perimeter that is partially opened,

the first component and the second component are in different vertical planes, and

the first and second components are arranged such that the openings in the perimeters of the first and second components are not superposed in a stacked state of the plural components.

Claim 7 (Previously Presented): A semiconductor device according to Claim 6, wherein an interconnection width of the shield is equal to or more than a size of a spacing of the spiral pattern of the inductor, and is equal to or less than a radius of the spiral pattern of the inductor.

Claim 8 (Previously Presented): A semiconductor device according to Claim 6, wherein a distance between the shield and an outer border of the interconnection of the inductor is equal to a spacing of the spiral pattern of the inductor.

Claim 9 (Currently Amended): A semiconductor device according to Claim 6, further comprising:

a plurality of interconnection layers formed on the semiconductor substrate, each of the plurality of interconnection layers corresponding to one of the plural planes, wherein the inductor is formed in any one of these interconnection layers; and

~~the shield~~ second conductor interconnection is formed in a different interconnection layer from the interconnection layer in which the inductor is formed.

Claim 10 (Previously Presented): A semiconductor device comprising:

a semiconductor substrate;

an inductor provided with a first conductor interconnection formed spirally on the semiconductor substrate; and

a shield that is provided with a second conductor interconnection in a ring having a continuous configuration provided along an inner periphery of the spiral pattern of the inductor except for an opening in a portion of the second conductor interconnection, and the second conductor is electrically connected to ground potential, wherein

said shield includes a plurality of components with the plural components extending in corresponding plural planes.

Claim 11 (Previously Presented): A semiconductor device according to Claim 10, wherein an interconnection width of the shield is equal to or less than a size of an interconnection width of the inductor.

Claim 12 (Canceled).